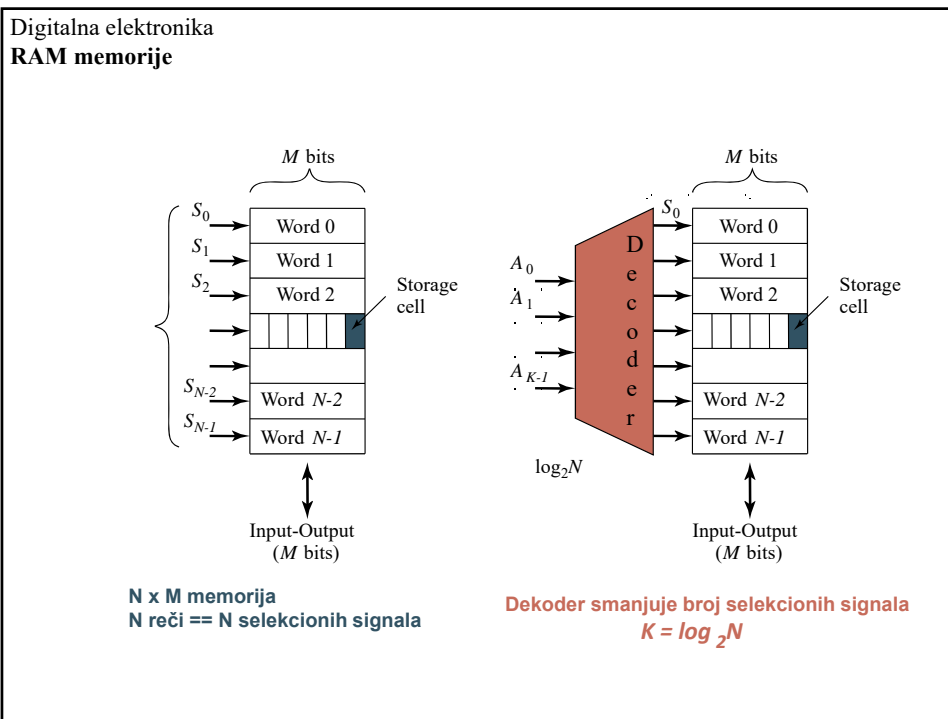
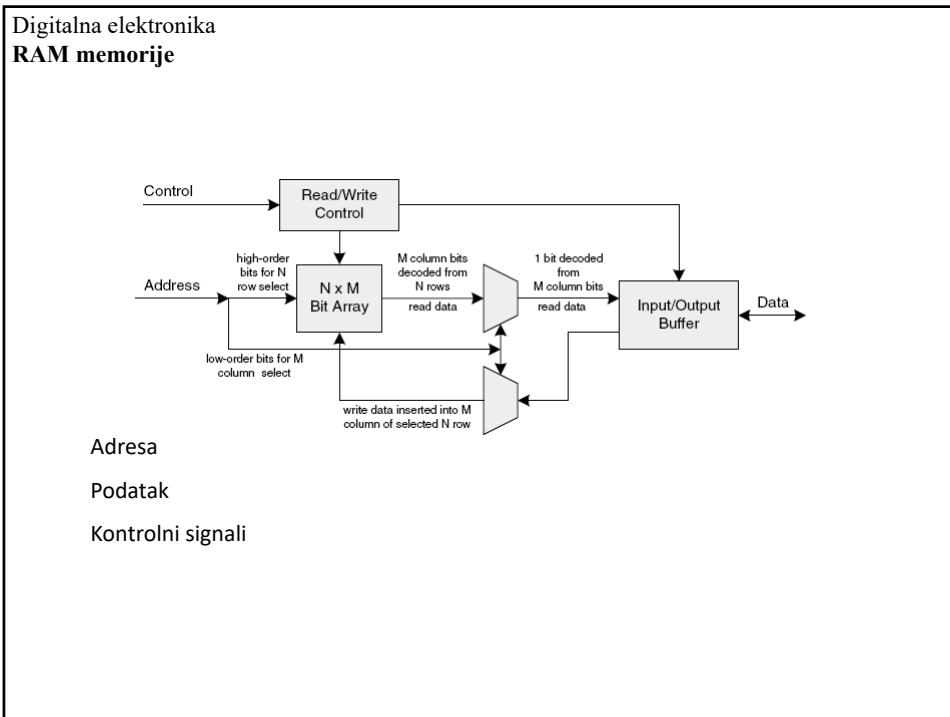
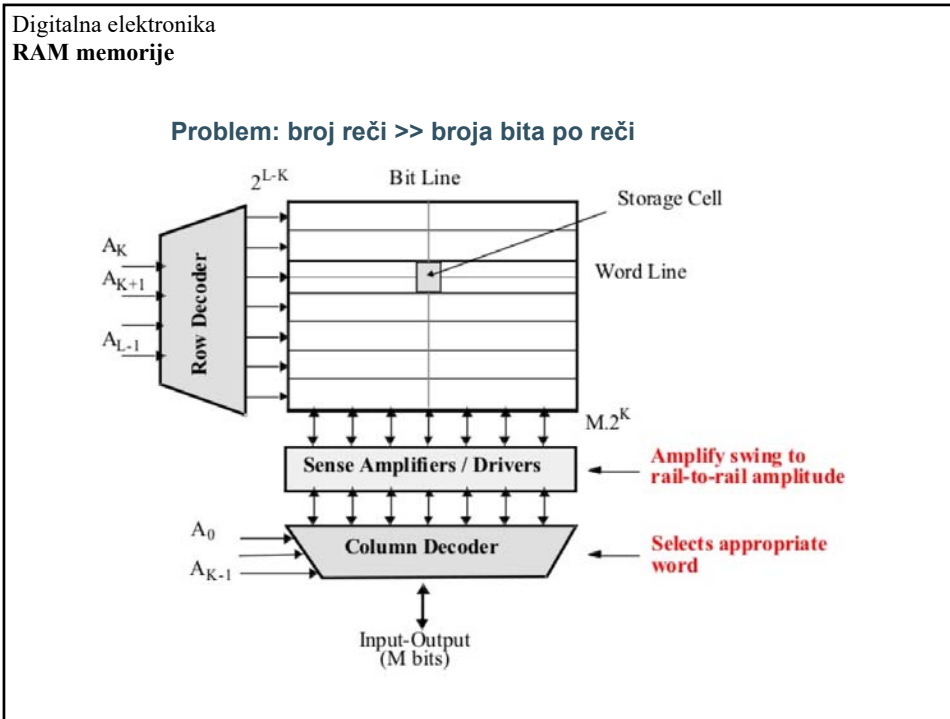


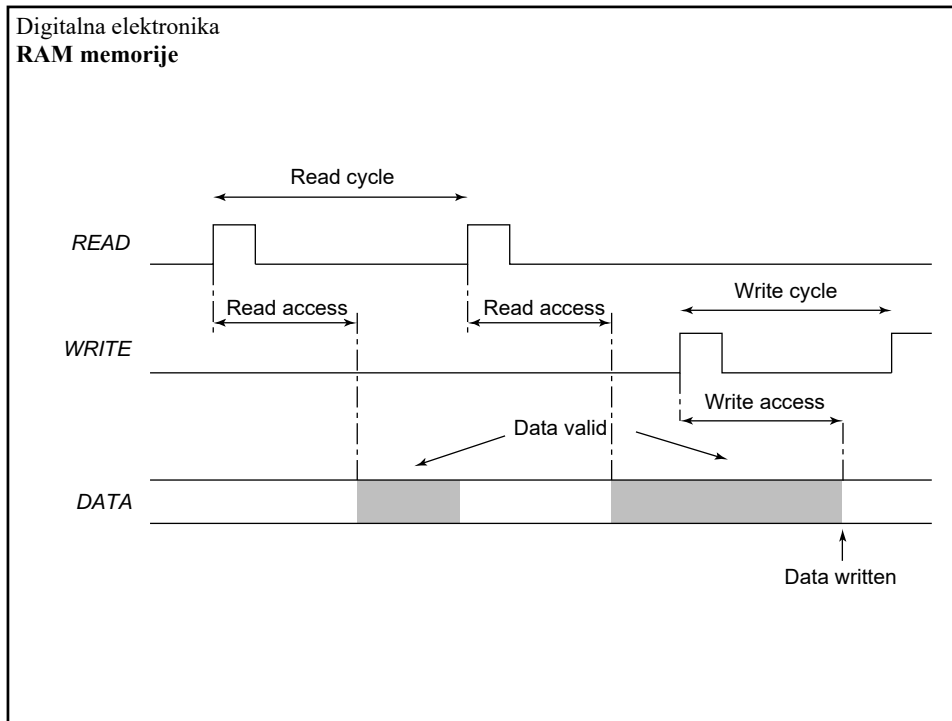
Digitalna elektronika  
RAM memorije

RWM Read-Write Memory		Non-Volatile Read-Write Memory	ROM Read-Only Memory
Random Access	Non-Random Access	EPROM E <sup>2</sup> PROM FLASH	Mask-Programmed Programmable (PROM)
SRAM  DRAM	FIFO  LIFO Shift Register  CAM		

NV RWM = NV RAM  
Ne gube sadržaj kada se isključi napajanje







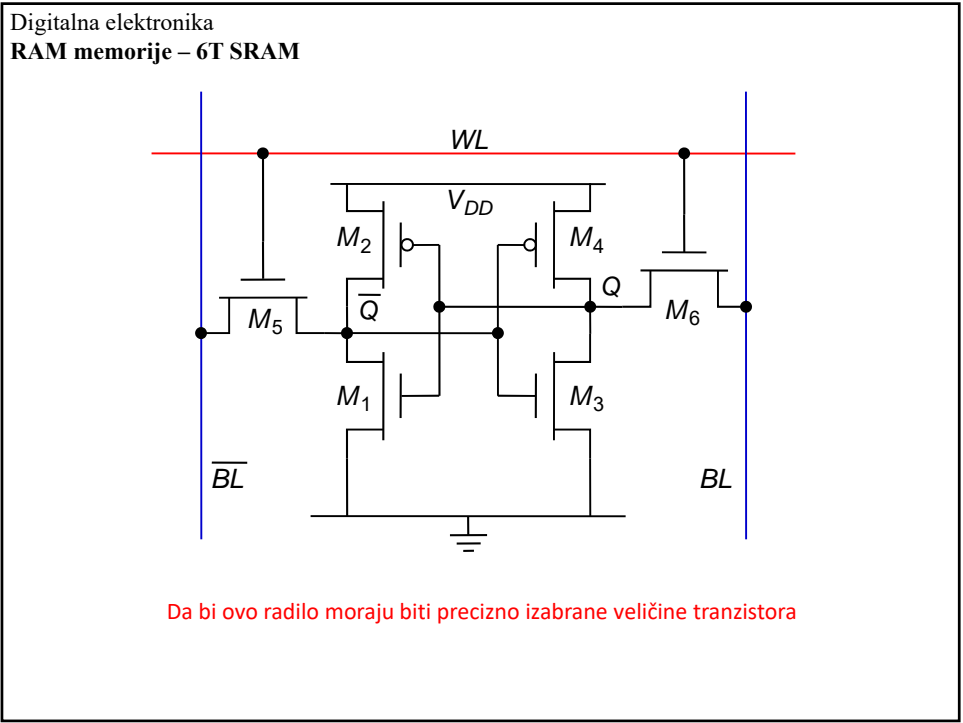
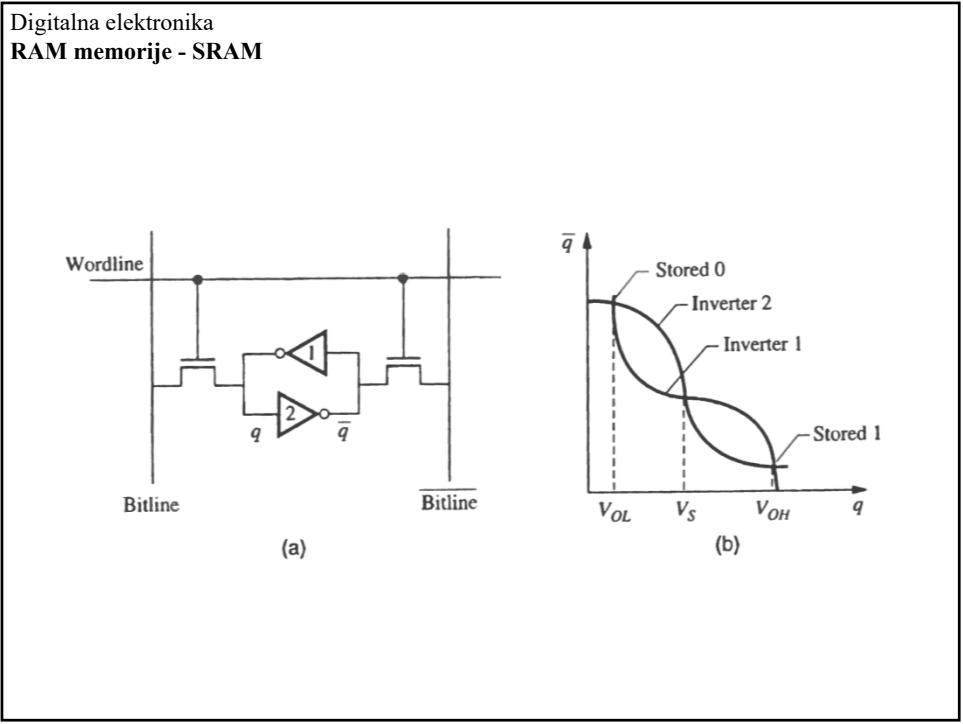
Digitalna elektronika  
RAM memorije

❑ **STATIC (SRAM)**

Podaci se pamte dok postoji napajanje  
Velika memorijska ćelija – 6 tranzistora  
Brze  
Memorijska ćelija ima diferencijalni izlaz

❑ **DYNAMIC (DRAM)**

Da bi podatak ostao sačuvan potrebno "osvežavanje"  
Mala memorijska ćelija – 1 do 3 tranzistora  
Sporije  
Memorijska ćelija ima jednostruki izlaz

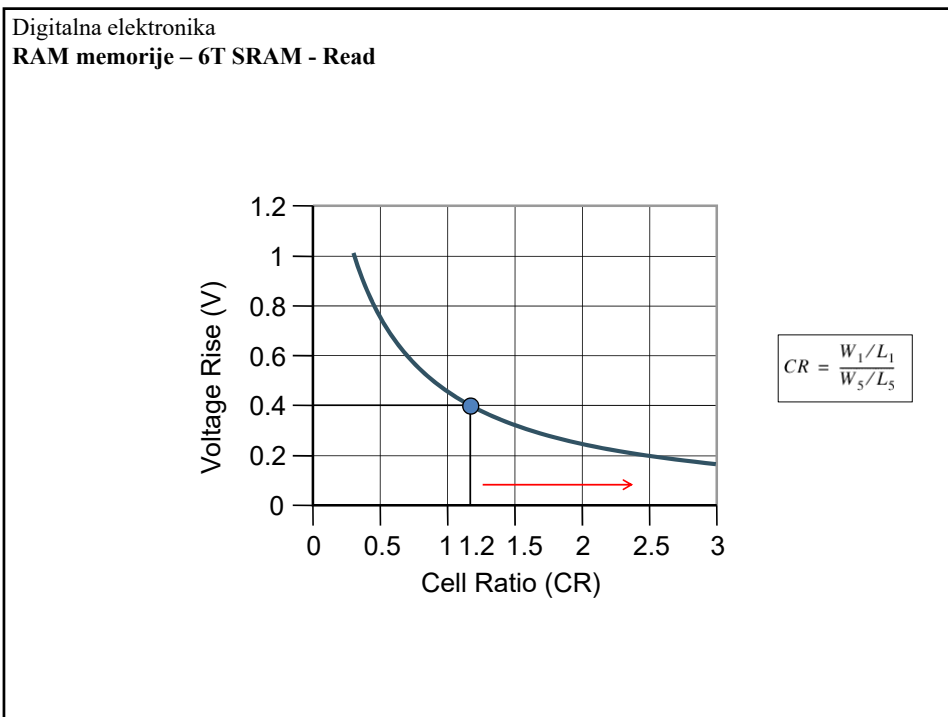


Digitalna elektronika  
RAM memorije – 6T SRAM - Read

Pre aktiviranja čitanja, bitske linije na  $V_{DD}$   
 $V_{DS1}$  ne sme da uključi M3,  $V_{GS3}$

$$I_{DS} = \frac{B_5}{2}(V_{GS5} - V_{Tn})^2 = I_{D1} = \frac{B_1}{2}(2V_{DS1}(V_{GS1} - V_{Tn}) - V_{DS1}^2)$$

$$(V_{DD} - V_{DS1} - V_{Tn})^2 = \frac{B_1}{B_5}(2V_{DS1}(V_{DD} - V_{Tn}) - V_{DS1}^2)$$

$$V_{DS1} = (V_{DD} - V_{Tn}) - \sqrt{(V_{DD} - V_{Tn})^2 - \frac{(V_{DD} - V_{Tn})^2}{(1 + CR)}}$$


Digitalna elektronika  
RAM memorije – 6T SRAM - Write

$$I_{D4} = \frac{B_4}{2}(V_{GS4} - V_{Tp})^2 = I_{D6} = \frac{B_6}{2}(2V_{DS6}(V_{GS6} - V_{Tn}) - V_{DS6}^2)$$

$$(-V_{DD} - V_{Tp})^2 = \frac{B_6}{B_4}(2V_{DS6}(V_{DD} - V_{Tn}) - V_{DS6}^2)$$

$$V_{DS6} = (V_{DD} - V_{Tn}) - \sqrt{(V_{DD} - V_{Tn})^2 - \frac{\mu_p}{\mu_n} PU (-V_{DD} - V_{Tp})^2}$$

Digitalna elektronika  
RAM memorije – 6T SRAM - Write

$$PU = \frac{W_4 / L_4}{W_6 / L_6}$$

Digitalna elektronika  
RAM memorije – Resistance load SRAM

$R_L$  veliko da bi se smanjila struja u statičkom režimu  
Koliko veliko?

Digitalna elektronika  
RAM memorije – TFT load SRAM

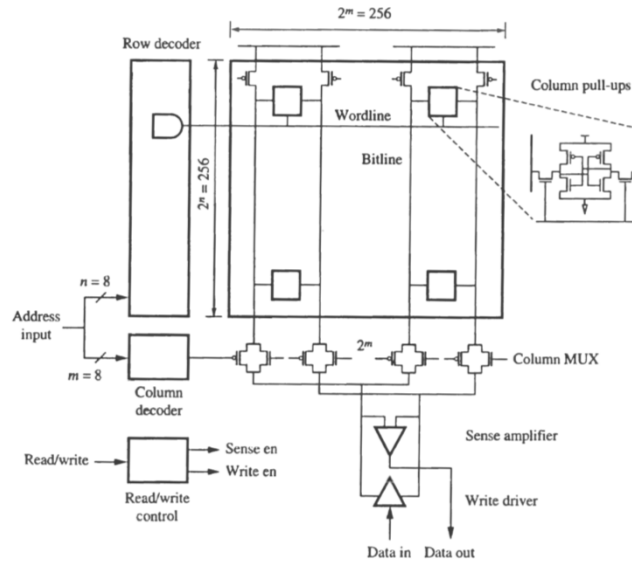
TFT - Thin Film Transistors - kao opterećenje

Digitalna elektronika  
RAM memorije – SRAM

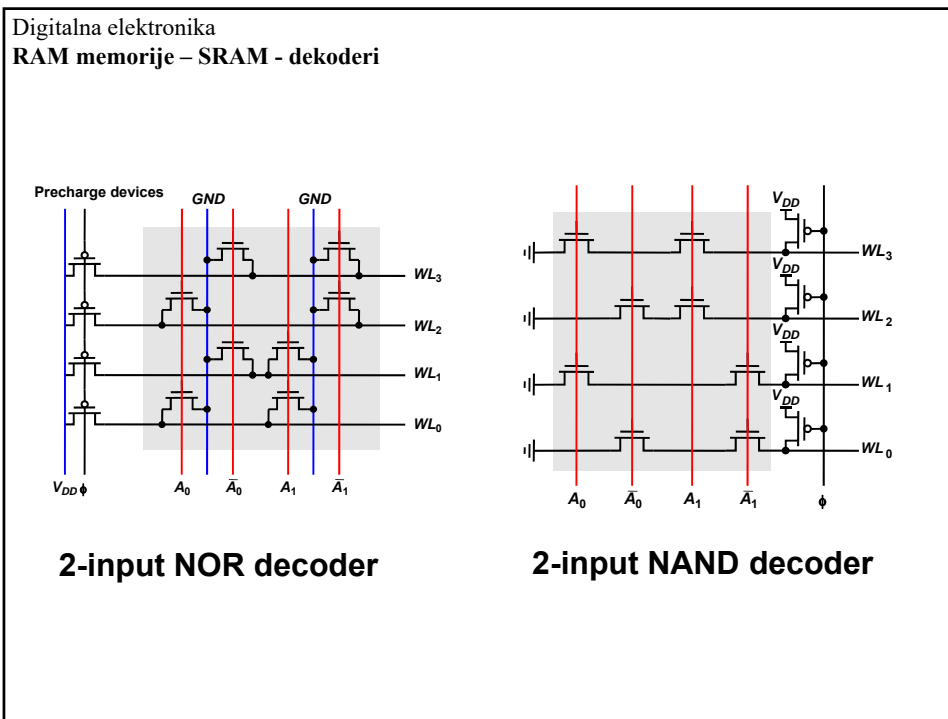
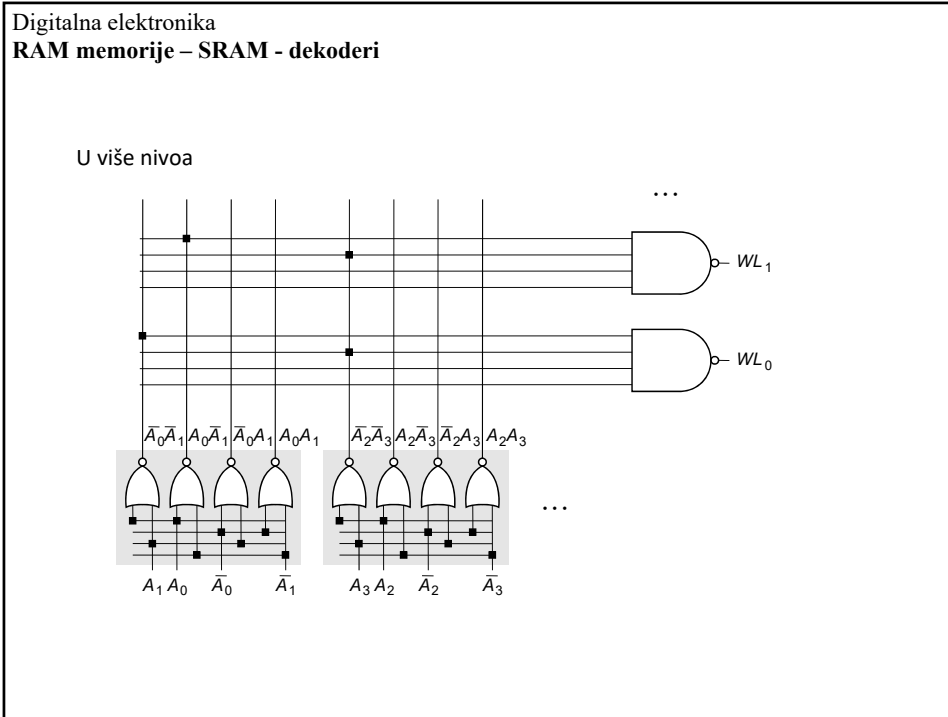
**Table 12-2** Comparison of CMOS SRAM cells used in 1-Mbit memory  
(from [Takada91])

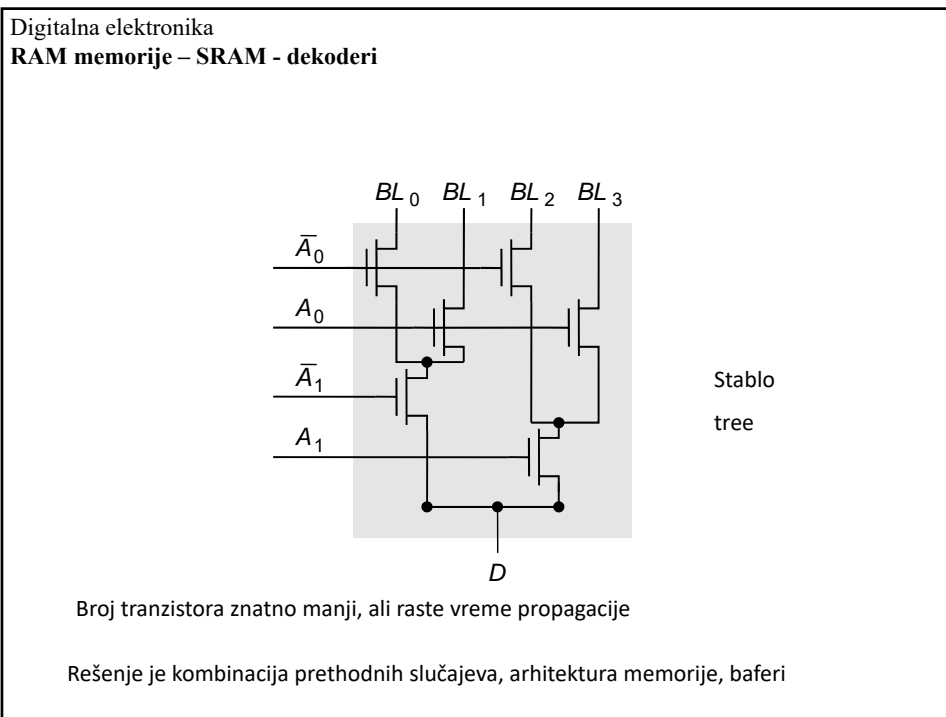
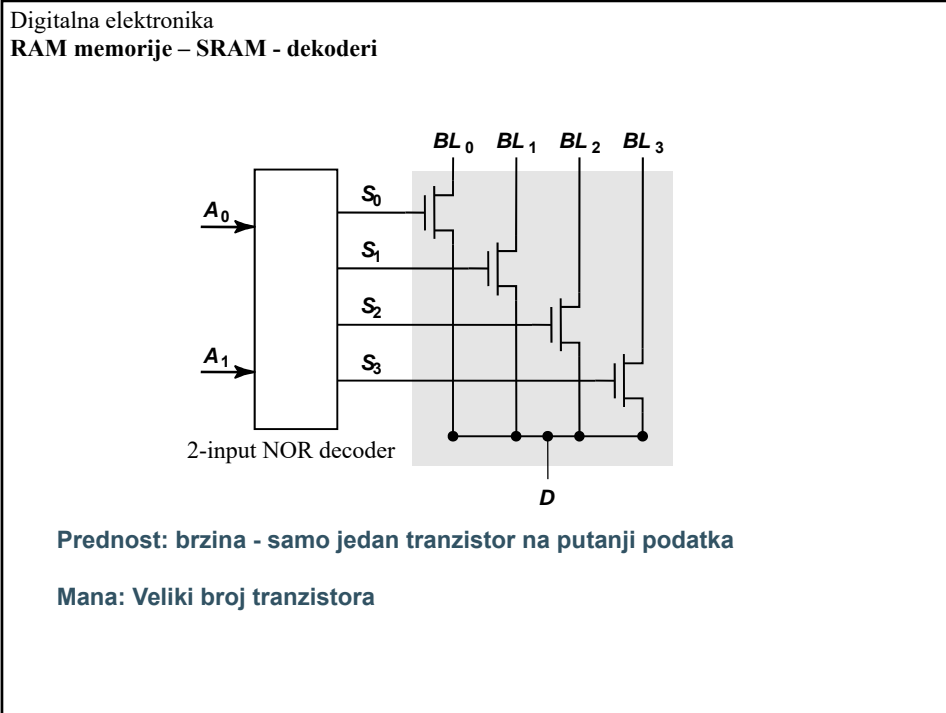
	Complementary CMOS	Resistive Load	TFT Cell
Number of transistors	6	4	4 (+2 TFT)
Cell size	58.2 $\mu\text{m}^2$ (0.7- $\mu\text{m}$ rule)	40.8 $\mu\text{m}^2$ (0.7- $\mu\text{m}$ rule)	41.1 $\mu\text{m}^2$ (0.8- $\mu\text{m}$ rule)
Standby current (per cell)	$10^{-15}$ A	$10^{-12}$ A	$10^{-13}$ A

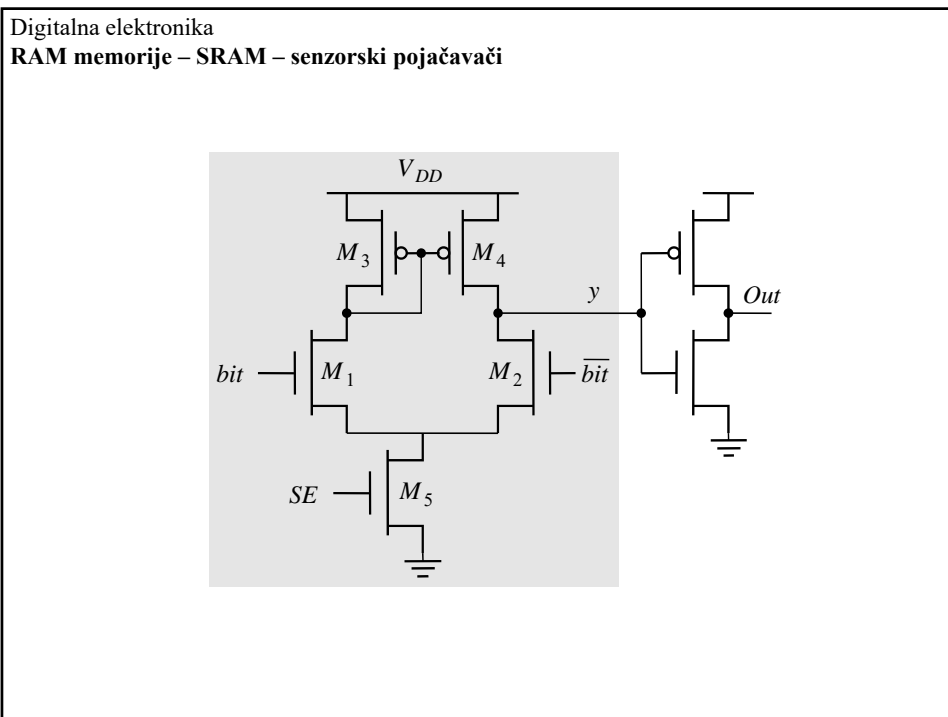
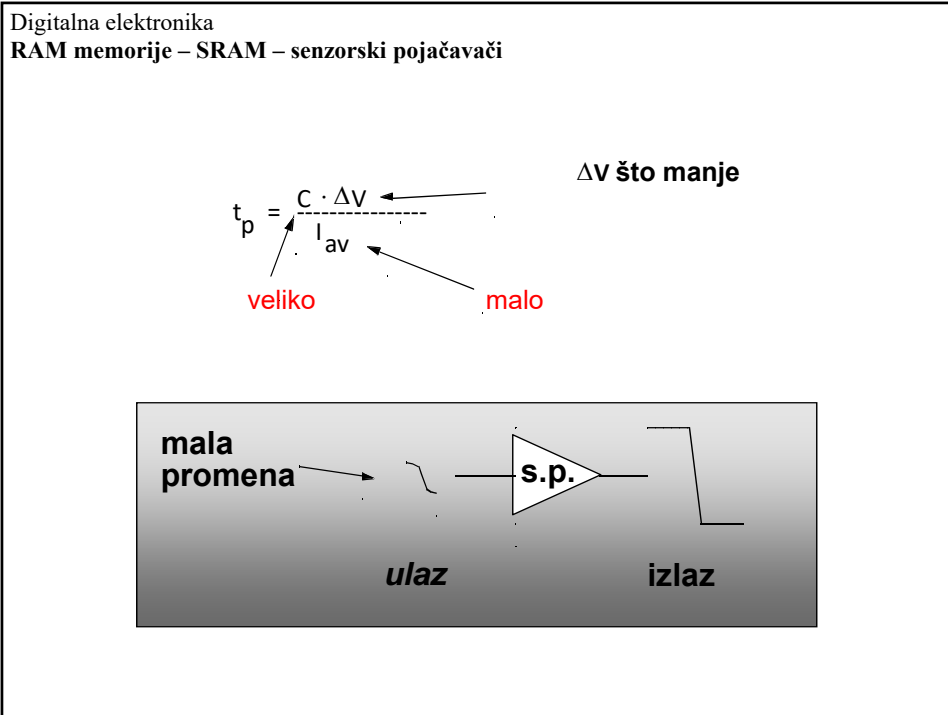
Digitalna elektronika  
RAM memorije – SRAM

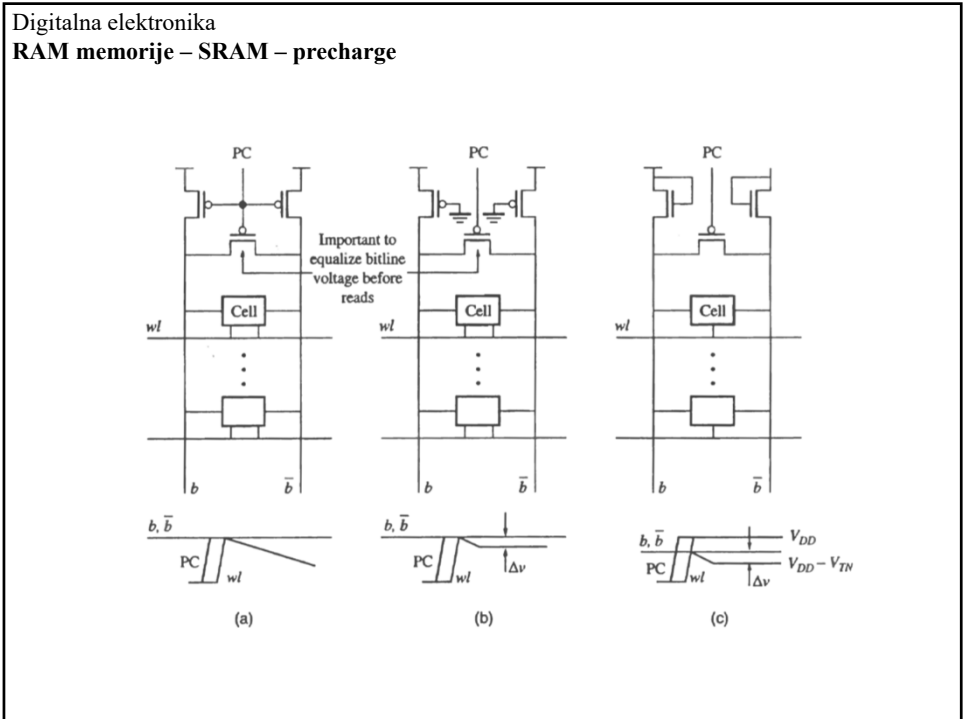
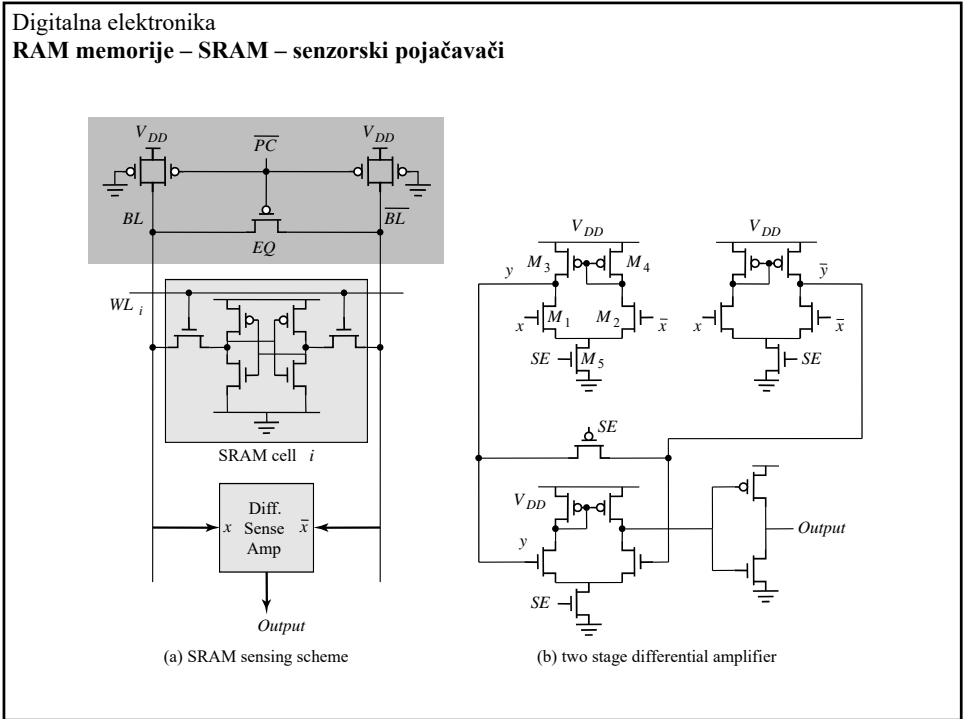


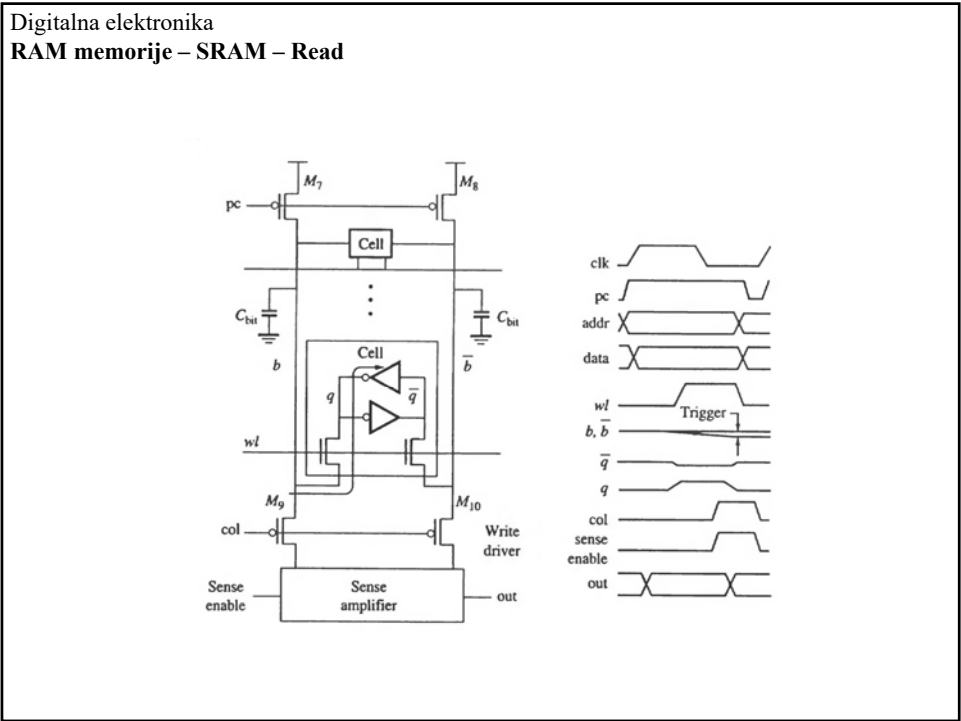
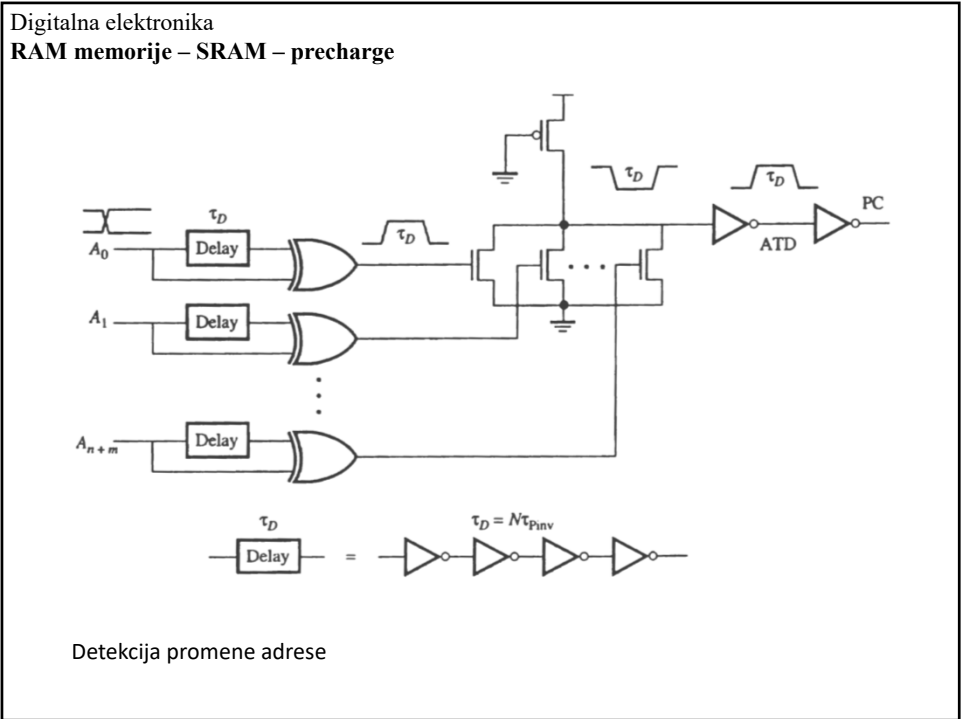


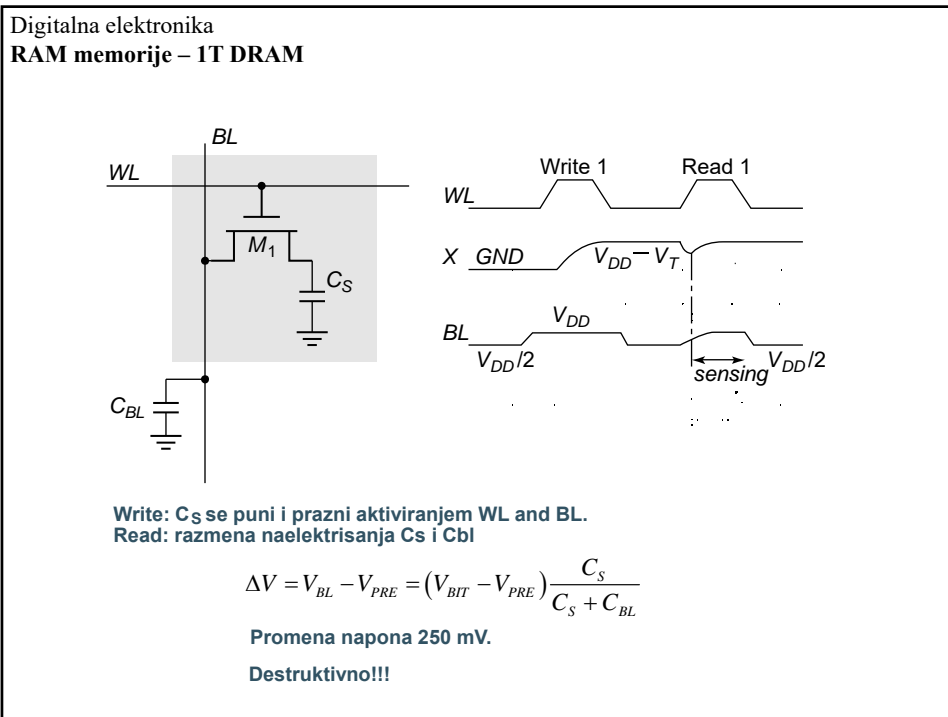
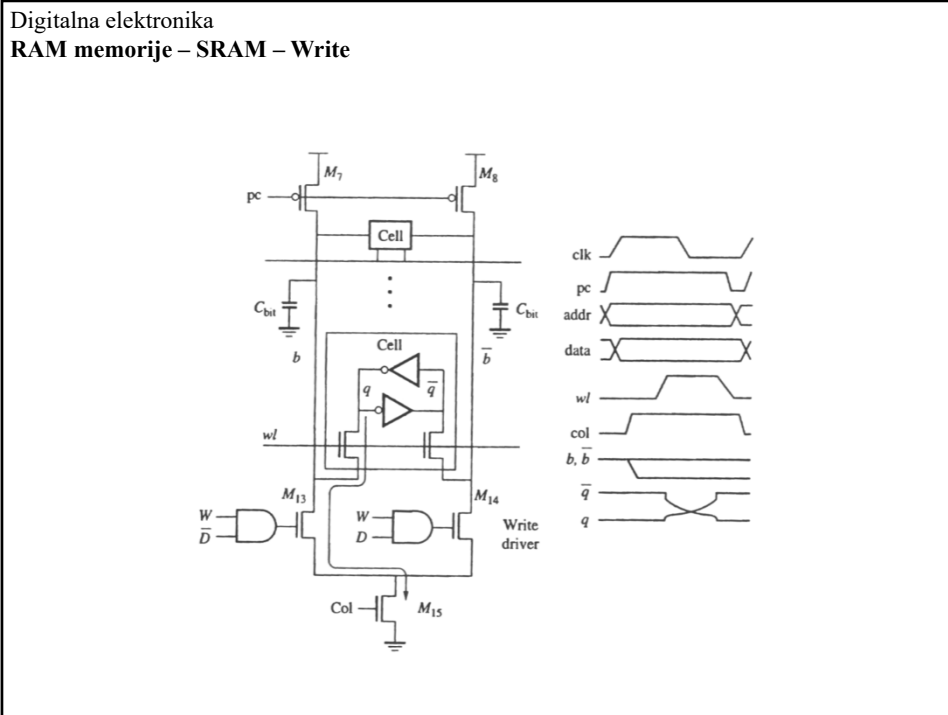


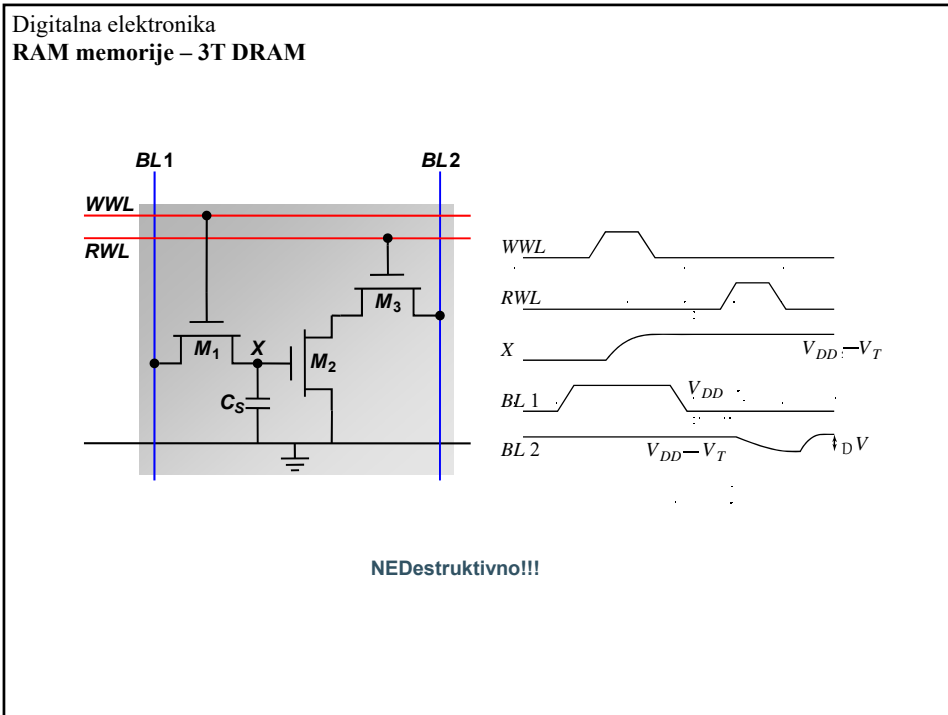












- Digitalna elektronika  
RAM memorije – DRAM
- 1T DRAM zahteva senzorski pojačavač
  - DRAM memorijska ćelija je sa jednostrukim izlazom - single ended.
  - SRAM ćelija je sa diferencijalnim izlazom.
  - Čitanje 1T DRAM ćelije je destruktivno; čitanje odnosno osvežavanje je neophodno.
  - Za razliku od 3T ćelije, 1T ćelija zahteva dodatnu kapacitivnost.
  - Kada se upisuje "1" u DRAM ćeliju napona na kondenzatoru je manji za napon praga MOS tranzistora, manje naelektrisanja,  $V_{wl} > V_{DD}$

